

Description

The NVMFS4C310NWFT1G uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = 30V I_{D} = 80A$

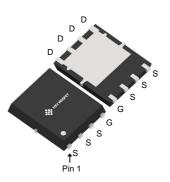
 $R_{DS(ON)} < 6m\Omega V_{GS}=10V$

Application

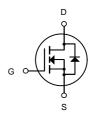
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L (SO-8-FL-5.8mm)



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
NVMFS4C310NWFT1G	DFN5X6-8L(SO-8-FL-58mm)	HXY MOSFET	5000

Absolute Maximum Ratings (T_C=25[°]C unless otherwise noted)

Symbol	Parameter	Rating	Units
Vos	Drain-Source Voltage	30	V
Vgs	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V	80	А
I _D @T _C =70°C	Continuous Drain Current, V _{GS} @ 10V	45	А
Ідм	Pulsed Drain Current ²	280	А
EAS	Single Pulse Avalanche Energy ³	56	mJ
P _D @T _C =25°C	Total Power Dissipation ⁴ 37		W
Тѕтс	Storage Temperature Range -55 to 150		°C
TJ	Operating Junction Temperature Range -55 to 150		°C
R _θ JA	A Thermal Resistance Junction-Ambient ¹		°C/W

NVMFS4C310NWFT1G

Electrical Characteristics (Tc=25°C Unless Otherwise Noted)

Symbol	Parameter	Condition	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-Source Breakdown Voltage	Vgs=0V ID=250μA	30			٧
	Zero Gate Voltage Drain Current	Vps=30V,Vgs=0V			0.1	μΑ
I _{DSS}	Zero Gate Voltage Drain Current(T _j =125°C)	Vps=30V,Vgs=0V			100	μΑ
Igss	Gate-Body Leakage Current	Vgs=±20V,Vps=0V			±100	nA
V _{GS(TH)}	Gate Threshold Voltage	Vps=Vgs,Ip=250μA	1.0	1.7	2.5	٧
R _{DS(ON)}	Drain-Source On-State Resistance③	Vgs=10V, ID=20A		4.7	6	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance③	Vgs=4.5V, ID=16A		5.4	8	mΩ
C _{iss}	Input Capacitance			1930		pF
Coss	Output Capacitance	V _{DS} =15V,V _{GS} =0V, f=1MHz		310		pF
C_{rss}	Reverse Transfer Capacitance			260		pF
R_g	Gate Resistance	f=1MHz		0.85		
Q_g	Total Gate Charge			38		nC
Q_{gs}	Gate-Source Charge	V _{DS} =15V,I _D =20A, V _{GS} =10V		5.1		nC
Q_{gd}	Gate-Drain Charge			12		nC
t _{d(on)}	Turn-on Delay Time			8.5		nS
t r	Turn-on Rise Time	V _{DD} =15V,		9		nS
t _{d(off)}	Turn-Off Delay Time	ID=20A,		31		nS
t _f	Turn-Off Fall Time	Rg=3, Vgs=10V		9		nS
V _{SD}	Forward on voltage	Isp=20A,Vgs=0V		0.8	1.2	٧
t _{rr}	Reverse Recovery Time	Tj=25°C,Isd=20A, VGS=0V		16		nS
Q _{rr}	Reverse Recovery Charge	di/dt=500A/μs		42		nC

NOTE:

- 1 Repetitive rating; pulse width limited by max. junction temperature.
- 2 Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH,R_G = 25 , I_{AS} = 15A, V_{GS} = 10V. Part not recommended for use above this value
- ③ Pulse width ≤ 300µs; duty cycle≤ 2%.



Typical Characteristics

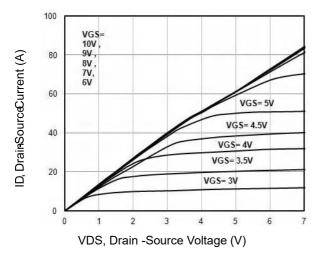


Fig1. Typical Output Characteristics

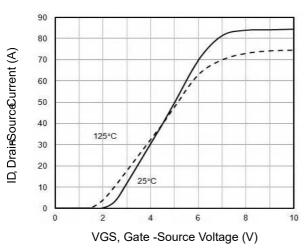


Fig3. Typical Transfer Characteristics

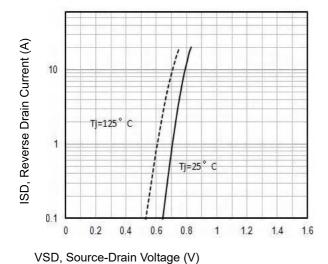


Fig6. Maximum Safe Operating Area Voltage

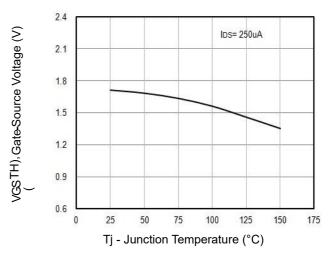
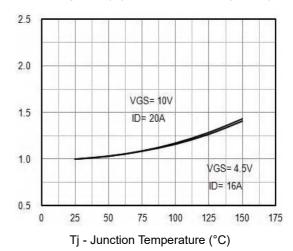


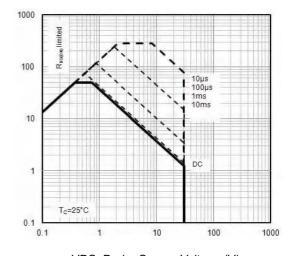
Fig2. V_{GS(TH)} Gate -Source Voltage Vs.Tj



Normalized On Resistance

D-Drain Current (A)

Fig4. Normalized On-Resistance Vs. Tj



VDS, Drain -Source Voltage (V)

Fig5. Typical Source-Drain Diode Forward

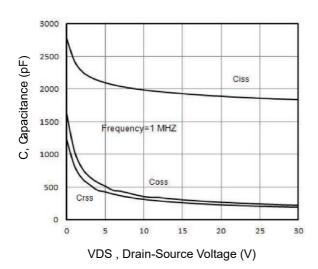


Fig7. Typical Capacitance Vs.Drain-Source Voltage

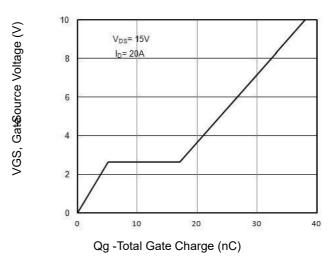


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

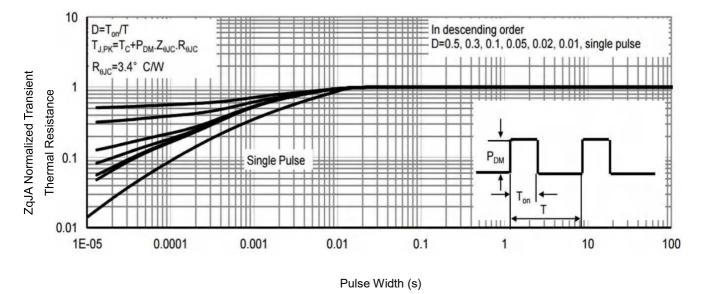


Fig9. Normalized Maximum Transient Thermal Impedance

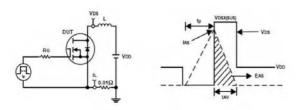


Fig10. Unclamped Inductive Test Circuit and waveforms

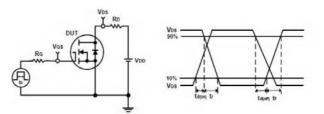
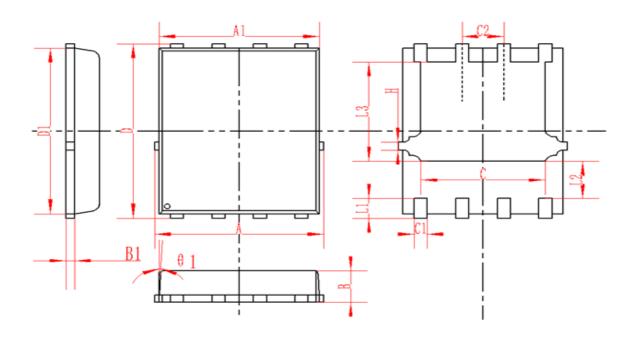


Fig11. Switching Time Test Circuit and waveforms

N-Channel Enhancement Mode MOSFET

DFN5X6-8L(SO-8-FL-5.8mm)Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010

NVMFS4C310NWFT1G

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